

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (previously presented) A semiconductor laser with a semiconductor body, including a laser resonator, comprising:

a plurality of discontinuities formed in a first region of said semiconductor body and arranged in an arrangement such that radiation generated by the semiconductor laser cannot propagate through said first region, and

a second region of said semiconductor body constituting the laser resonator, said second region being formed by an interruption of said arrangement and having none of said discontinuities formed therein, to enable propagation of radiation generated by the semiconductor laser through said second region.

2. (previously presented) The semiconductor laser as claimed in claim 1, wherein the resonator has an angled or curved resonator axis.

3. (previously presented) The semiconductor laser as claimed in claim 1, wherein the discontinuities are filled with a filling material, a refractive index of said filling material being different from a refractive index of said semiconductor body.

4. (previously presented) The semiconductor laser as claimed in claim 1, wherein said first and second semiconductor body regions adjoin a filling material, a refractive index of said filling material being different from a refractive index of said first and second semiconductor body regions.

5. (previously presented) An optically pumped semiconductor device with a vertical emitter comprising a quantum well structure, wherein said quantum well structure of said vertical emitter is optically pumped by at least one semiconductor laser as claimed in claim 1.

6. (previously presented) An optically pumped semiconductor device with a vertical emitter comprising a quantum well structure wherein said quantum well structure of said vertical emitter is pumped by a plurality of semiconductor lasers as claimed in claim 1, at least one of said semiconductor lasers having a resonator with an angled or curved resonator axis.

7. (previously presented) An optically pumped semiconductor device with a vertical emitter comprising a quantum well structure, and with a pump radiation source, which generates pump radiation for optically pumping said quantum well structure, comprising:

 a waveguide for coupling said pump radiation into said quantum well structure, wherein said waveguide is laterally delimited at least partly by an arrangement of a plurality of discontinuities arranged in such a way that said pump radiation is not capable of propagating within said arrangement.

8. (previously presented) The optically pumped semiconductor device as claimed in claim 7, wherein said discontinuities are filled with a filling material, a refractive index of said filling material being different from a refractive index of said semiconductor body.

9. (previously presented) The optically pumped semiconductor device as claimed in claim 7, wherein said semiconductor regions adjoin a filling material, a refractive index of said filling material being different from a refractive index of said semiconductor regions.

10. (currently amended) The optically pumped semiconductor device as claimed in claim 7, wherein said pump radiation source is a semiconductor laser with a semiconductor body, including a laser resonator, comprising:

a first region of said semiconductor body, the [[a]] plurality of discontinuities being formed in [[a]] said first region of said semiconductor body and arranged such that radiation generated by said semiconductor laser cannot propagate through said first region, and

a second region of said semiconductor body constituting said laser resonator, said second region having none of said discontinuities formed therein, to enable propagation of radiation generated by the semiconductor laser through said second region.

11. (previously presented) The optically pumped semiconductor device as claimed in claim 5, wherein said vertical emitter and said semiconductor laser are grown epitaxially on a common substrate.

12. (previously presented) The optically pumped semiconductor device as claimed in claim 7, wherein said vertical emitter and said pump radiation source are grown epitaxially on a common substrate.

13. (original) The optically pumped semiconductor device as claimed in claim 7, wherein said discontinuities comprise a periodic arrangement of cutouts.

14. (original) The optically pumped semiconductor device as claimed in claim 7, wherein said discontinuities comprise a periodic arrangement of semiconductor regions.

15. (original) The semiconductor laser as claimed in claim 1, wherein said discontinuities comprise a periodic arrangement of cutouts.

16. (original) The semiconductor laser as claimed in claim 1, wherein said discontinuities comprise a periodic arrangement of semiconductor regions.

17. (previously presented) The semiconductor as claimed in claim 1, wherein said semiconductor body comprises outer side areas forming resonator mirrors of said laser resonator.

18. (previously presented) The optically pumped semiconductor device as claimed in claim 7, wherein said waveguide and said quantum well structure are monolithically integrated.

19. (currently amended) The optically pumped semiconductor device as claimed in claim 10, ~~wherein said discontinuities are arranged in an arrangement~~, said second region being formed [[by]] as an interruption of said arrangement of discontinuities.